

COMPENSATED IMPURITY CONDUCTIVITY
OF SINGLE CRYSTALS $\text{Cd}_{1-x}\text{Zn}_x\text{Te}$

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S u m m a r y

We have studied the mechanism of conductivity of single crystals $\text{Cd}_{1-x}\text{Zn}_x\text{Te}$ ($x = 0.05$) with regard for deep acceptor impurities (defects) of several types and their compensation by donors and determined the ionization energy and the compensation level for acceptors responsible for the material conductivity. The optimum conditions for increasing the resistivity depending on the impurity ionization level are formulated.